

- 2 A Continuous On-State Current
- 15 A Surge-Current
- Glass Passivated Wafer
- 400 V to 600 V Off-State Voltage
- Max I_{GT} of 200 μ A
- Package Options

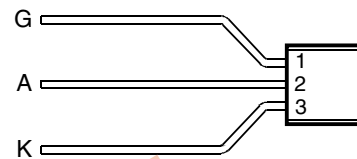
PACKAGE	PACKING	PART # SUFFIX
LP	Bulk	(None)
LP with formed leads	Tape and Reel	R

**LP PACKAGE
(TOP VIEW)**



MDC1AA

**LP PACKAGE
WITH FORMED LEADS
(TOP VIEW)**



MDC1AB

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TICP106D	V_{DRM}	400	V
	TICP106M		600	
Repetitive peak reverse voltage	TICP106D	V_{RRM}	400	V
	TICP106M		600	
Continuous on-state current at (or below) 25°C case temperature (see Note 2)		$I_{T(RMS)}$	2	A
Surge on-state current (see Note 3)		I_{TSM}	15	A
Peak positive gate current (pulse width \leq 300 μ s)		I_{GM}	0.2	A
Average gate power dissipation (see Note 4)		$P_{G(AV)}$	0.3	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply when the gate-cathode resistance $R_{GK} = 1 \text{ k}\Omega$.
 2. These values apply for continuous dc operation with resistive load. Above 25°C derate linearly to zero at 110°C.
 3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
 4. This value applies for a maximum averaging time of 20 ms.

PRODUCT INFORMATION

MARCH 1988 - REVISED SEPTEMBER 2002
 Specifications are subject to change without notice.

**TICP106 SERIES
SILICON CONTROLLED RECTIFIERS**

BOURNS®

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM}	Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$R_{GK} = 1 \text{ k}\Omega$				20	μA
I_{RRM}	Repetitive peak reverse current	$V_R = \text{rated } V_{RRM}$	$I_G = 0$				200	μA
I_{GT}	Gate trigger current	$V_{AA} = 12 \text{ V}$	$R_L = 100 \Omega$	$t_{p(g)} \geq 20 \mu\text{s}$		5	200	μA
V_{GT}	Gate trigger voltage	$V_{AA} = 12 \text{ V}$	$R_L = 100 \Omega$ $R_{GK} = 1 \text{ k}\Omega$	$t_{p(g)} \geq 20 \mu\text{s}$	0.4		1	V
I_H	Holding current	$V_{AA} = 12 \text{ V}$	$R_{GK} = 1 \text{ k}\Omega$	Initiating $I_T = 10 \text{ mA}$			5	mA
V_T	On-state voltage	$I_T = 1 \text{ A}$	(see Note 5)				1.5	V

NOTE 5: This parameter must be measured using pulse techniques, $t_p = 1 \text{ ms}$, duty cycle $\leq 2 \%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

OBSOLETE

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